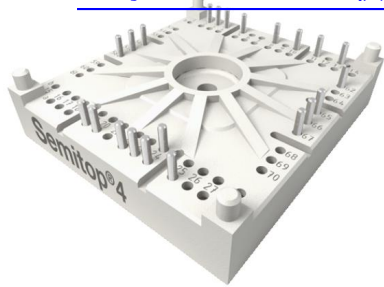


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SEMITOP® 4

IGBT Module

SK200GD066T

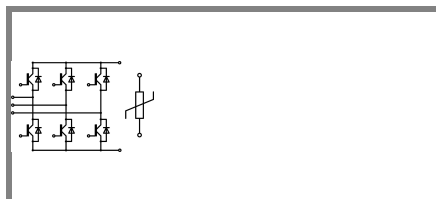
Target Data

Features

- One screw mounting module
- Fully compatible with SEMITOP®1,2,3
- Improved thermal performances by aluminium oxide substrate
- Trench IGBT technology
- CAL technology FWD
- Integrated NTC temperature sensor

Typical Applications

- Inverter up to 42 kVA
- Typ. motor power 18,5 kW



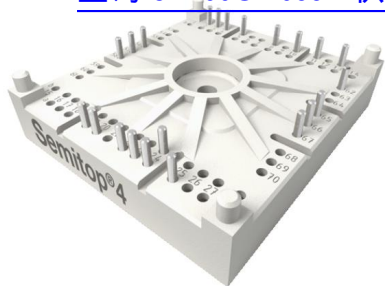
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Absolute Maximum Ratings		T _s = 25 °C, unless otherwise specified	
Symbol	Conditions	Values	Units
IGBT			
V _{CES}	T _j = 25 °C	600	V
I _C	T _j = 175 °C	T _s = 25 °C	174 A
		T _s = 70 °C	131 A
I _{CRM}	I _{CRM} = 2 × I _{Cnom}	400	A
V _{GES}		± 20	V
t _{psc}	V _{CC} = 360 V; V _{GE} ≤ 20 V; T _j = 125 °C V _{CES} < 600 V	6	µs
Inverse Diode			
I _F	T _j = 175 °C	T _s = 25 °C	99 A
		T _s = 70 °C	79 A
I _{FRM}	I _{FRM} = 2 × I _{Fnom}	120	A
Module			
I _{t(RMS)}			A
T _{vj}		-40 ... +150	°C
T _{stg}		-40 ... +125	°C
V _{isol}	AC, 1 min.	2500	V

Characteristics		T _s = 25 °C, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT					
V _{GE(th)}	V _{GE} = V _{CE} , I _C = 3,2 mA	5	5,8	6,5	V
I _{CES}	V _{GE} = 0 V, V _{CE} = V _{CES}	T _j = 25 °C			mA
		T _j = 125 °C			mA
I _{GES}	V _{CE} = 0 V, V _{GE} = 20 V	T _j = 25 °C		1200	nA
		T _j = 125 °C			nA
V _{CE0}		T _j = 25 °C	0,6	1	V
		T _j = 150 °C	0,7	0,8	V
r _{CE}	V _{GE} = 15 V	T _j = 25 °C	2,75	4	mΩ
		T _j = 150 °C	4,25	5,5	mΩ
V _{CE(sat)}	I _{Cnom} = 200 A, V _{GE} = 15 V	T _j = 25 °C _{chiplev.}	1,45	1,9	V
		T _j = 150 °C _{chiplev.}	1,7	2,15	V
C _{ies}	V _{CE} = 25, V _{GE} = 0 V	f = 1 MHz	12,2		nF
C _{oes}			0,76		nF
C _{res}			0,36		nF
t _{d(on)}	R _{Gon} = 22 Ω di/dt = 2575 A/µs	V _{CC} = 300V I _{Cnom} = 200A	134		ns
t _r			125		ns
E _{on}	R _{Goff} = 22 Ω di/dt = 2575 A/µs	T _j = 125 °C V _{GE} = -7/+15 V	17,6		mJ
t _{d(off)}			1131		ns
t _f			86		ns
E _{off}			11,8		mJ
R _{th(j-s)}	per IGBT		0,45		K/W

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SEMITOP® 4

IGBT Module

SK200GD066T

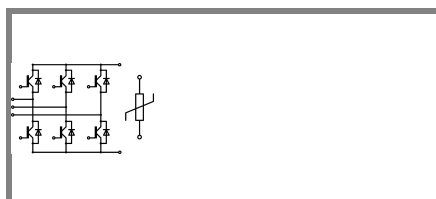
Target Data

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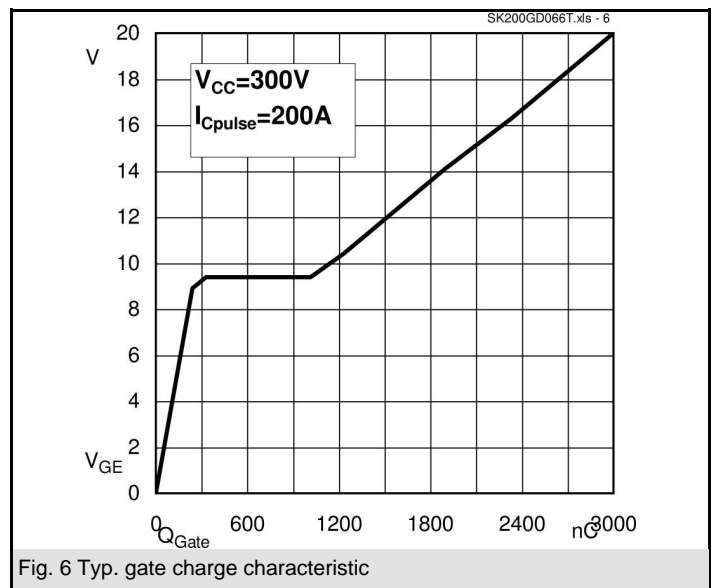
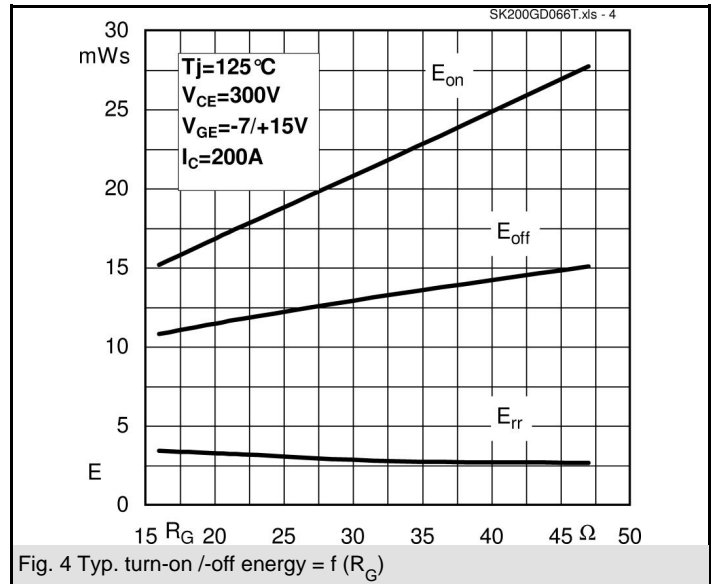
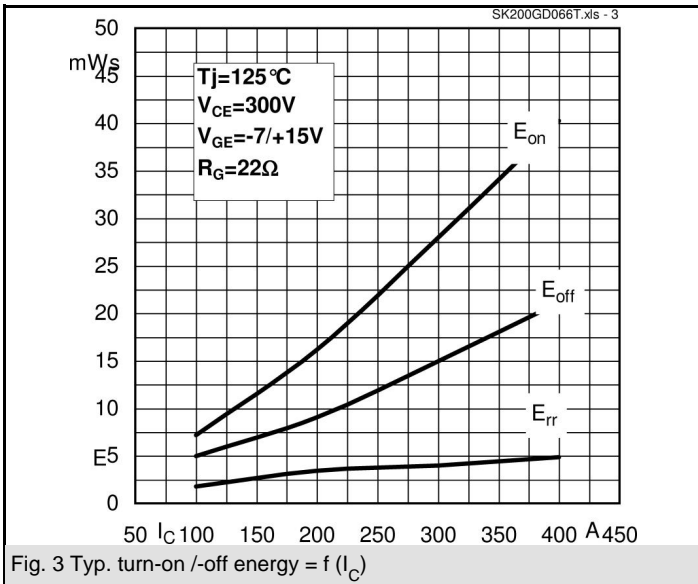
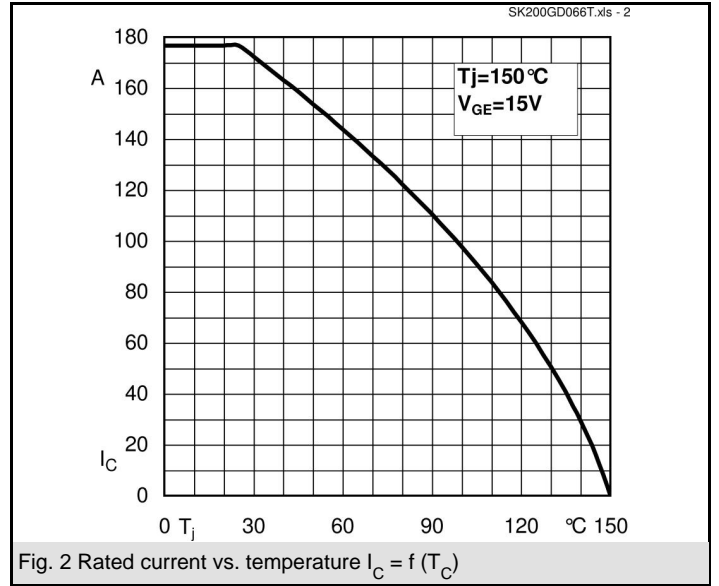
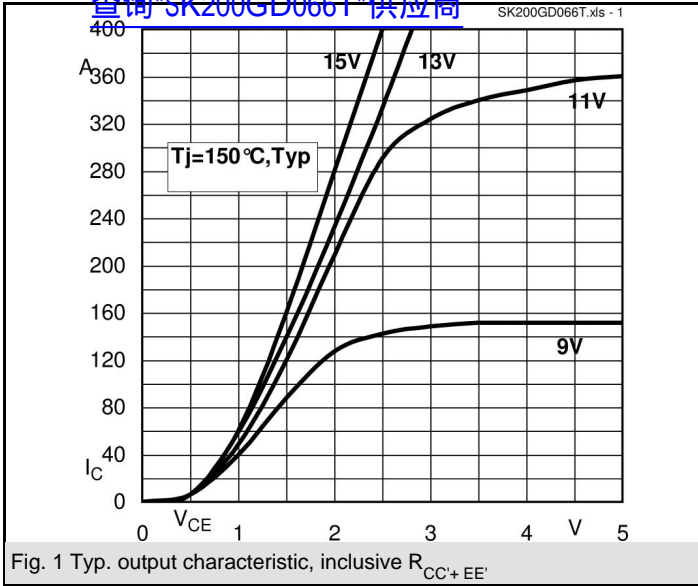
Characteristics

Symbol	Conditions	min.	typ.	max.	Units
Inverse Diode					
$V_F = V_{EC}$	$I_{Fnom} = 200 \text{ A}; V_{GE} = 0 \text{ V}$		$T_j = 25 \text{ }^\circ\text{C}_{\text{chiplev.}}$	1,48	V
			$T_j = 150 \text{ }^\circ\text{C}_{\text{chiplev.}}$	1,5	V
V_{F0}			$T_j = 25 \text{ }^\circ\text{C}$	0,95	V
			$T_j = 150 \text{ }^\circ\text{C}$	0,85	V
r_F			$T_j = 25 \text{ }^\circ\text{C}$	3	mΩ
			$T_j = 150 \text{ }^\circ\text{C}$	3,5	mΩ
I_{RRM}	$I_{Fnom} = 200 \text{ A}$	$T_j = 125 \text{ }^\circ\text{C}$	80		A
Q_{rr}	$di/dt = 2575 \text{ A}/\mu\text{s}$		20		μC
E_{rr}	$V_{CC} = 300\text{V}$		3,2		mJ
$R_{th(j-s)D}$	per diode		0,8		K/W
M_s	to heat sink			3,5	Nm
w			60		g
Temperature sensor					
R_{100}	$T_s = 100^\circ\text{C} (R_{25} = 5\text{k}\Omega)$		493±5%		Ω

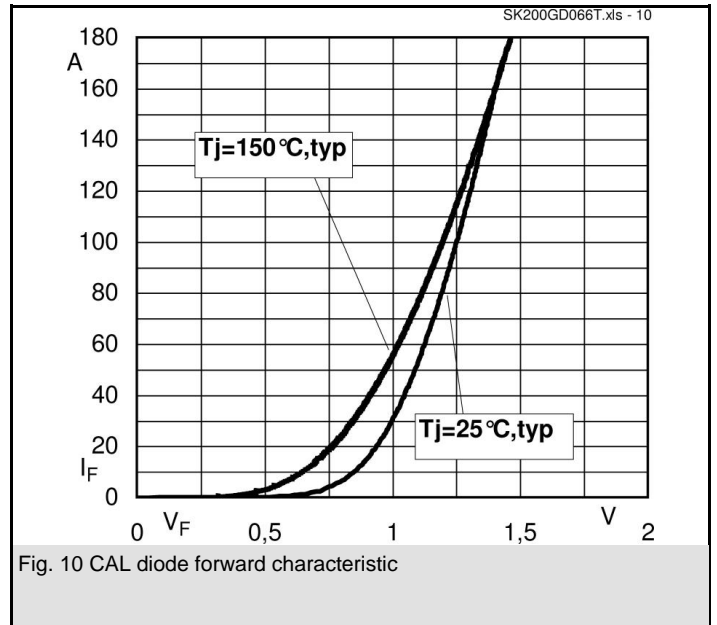
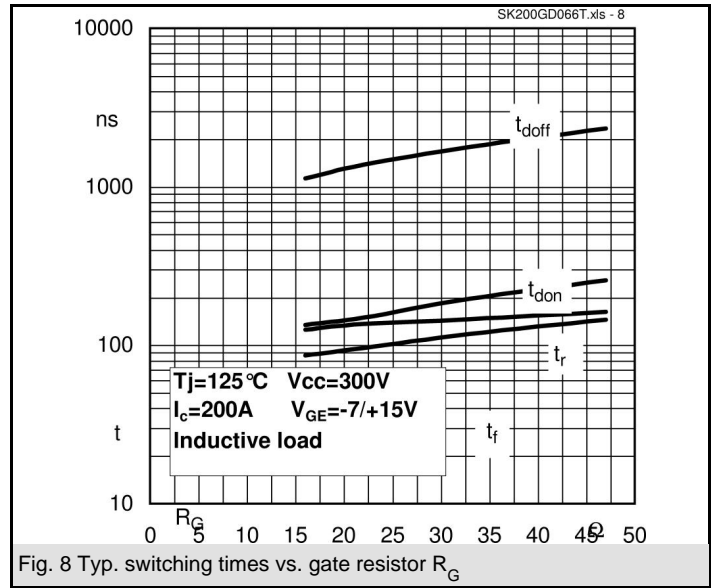
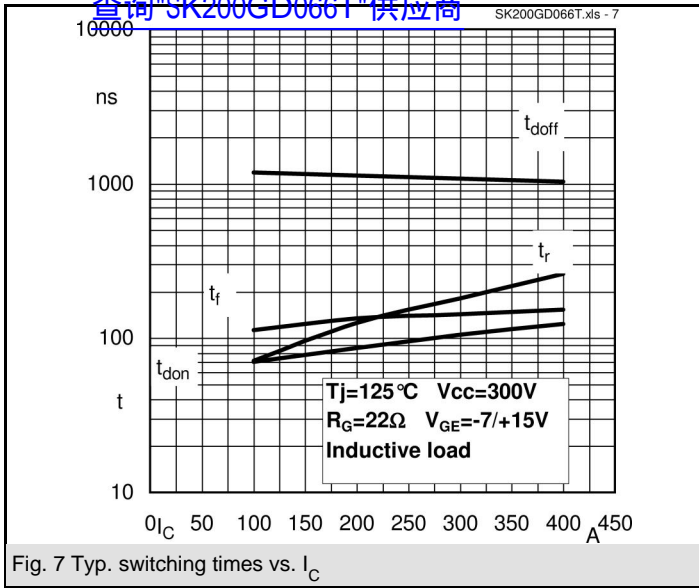
This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.

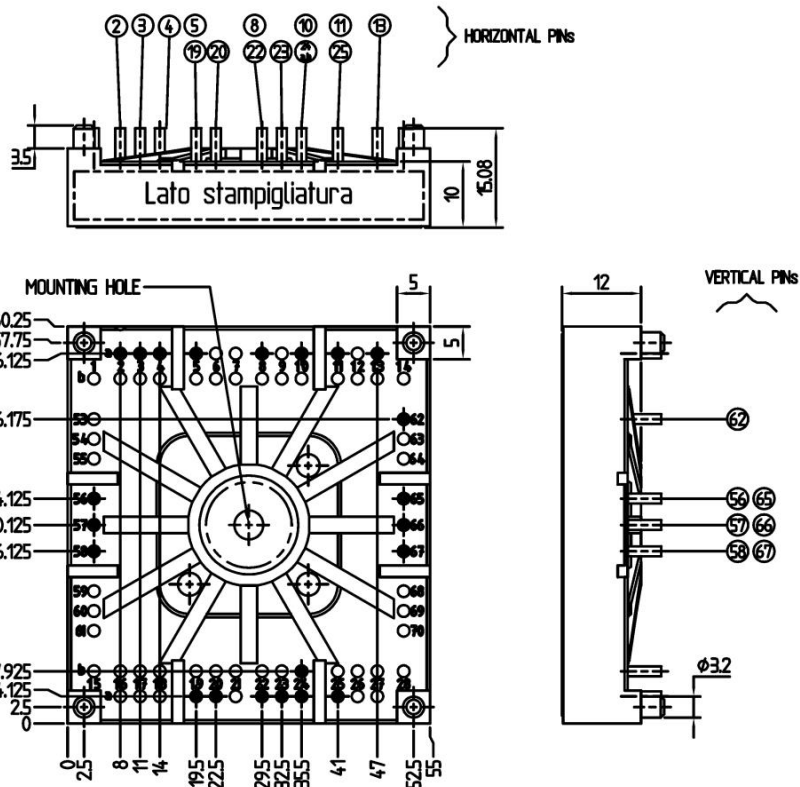
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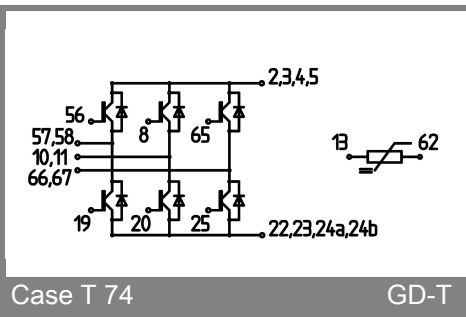
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Case T74 (Suggested hole diameter for the solder pins in the circuit board: 2mm. Suggested hole diameter for the mounting pins in the circuit board: 3,6mm)



Case T 74

GD-T